

N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Q	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{sp} = 25 °C; <u>Fig. 2; Fig. 3</u>	-	-	7	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	-	8	W
Static chara	acteristics	· · · · · ·				
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C	-	-	84	mΩ
	resistance	V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C	-	62	72	mΩ
		V _{GS} = 5 V; I _D = 8 A; T _j = 25 °C; <u>Fig. 12;</u> <u>Fig. 13</u>	-	64	75	mΩ
Avalanche r	ruggedness	·				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\begin{split} I_D &= 7 \text{ A}; \text{V}_{\text{sup}} \leq 100 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 5 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$	-	-	49	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G-UFT 4
4	D	drain	L1 L2 L3 SC-73 (SOT223)	mbb076 S

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK9875-100A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			
BUK9875-100A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9875-100A	987510A
BUK9875-100A/CU	987510

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-10	10	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	8	W
I _D	drain current	T _{sp} = 25 °C; V _{GS} = 5 V; <u>Fig. 2; Fig. 3</u>	-	7	А
		T _{sp} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	4	А
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 3	-	28	А

BUK9875-100A

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Symbol	Parameter	Conditions	Min	Мах	Unit
T _{stg}	storage temperature		-55	150	°C
Tj	junction temperature		-55	150	°C
V _{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \ \mu s$	-15	15	V
Source-drai	in diode				
I _S	source current	T _{sp} = 25 °C	-	7	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^\circ C$	-	28	А
Avalanche i	ruggedness	· · ·			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D = 7 \text{ A}; \ V_{sup} &\leq 100 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} &= 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{split}$	-	49	mJ

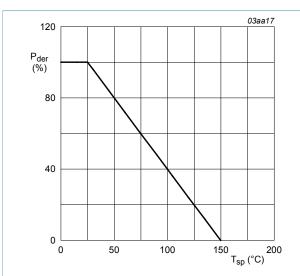


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

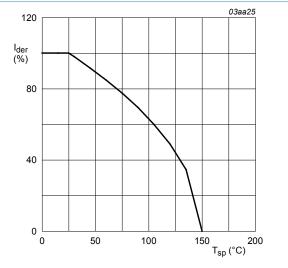
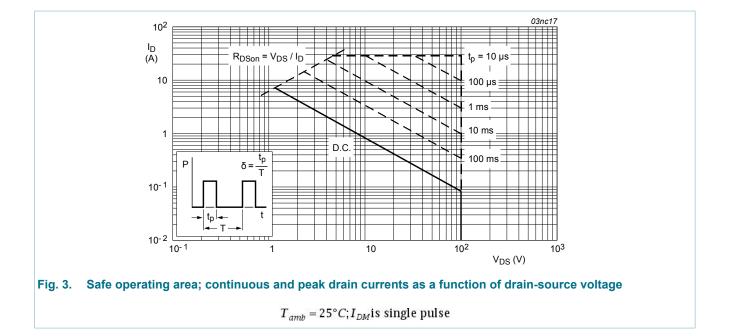


Fig. 2. Normalized continuous drain current as a function of solder point temperature

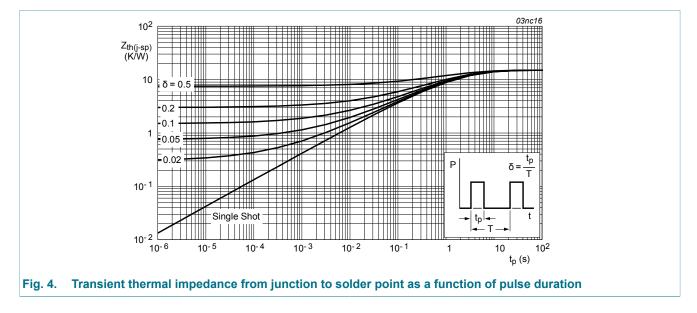
$$I_{der} = \frac{I_D}{I_{D(25^\circ \text{C})}} \times 100\%$$

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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	<u>Fig. 4</u>		-	120	-	K/W



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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; <u>Fig. 11</u>	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 11	-	-	2.3	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 150 °C; Fig. 11	0.6	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 8 A; T _j = 150 °C; Fig. 12; Fig. 13	-	-	162	mΩ
		V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C	-	-	84	mΩ
		V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C	-	62	72	mΩ
		V _{GS} = 5 V; I _D = 8 A; T _j = 25 °C; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	64	75	mΩ
Dynamic ch	aracteristics	· · · · · · · · · · · · · · · · · · ·	I			
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1270	1690	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	140	167	pF
C _{rss}	reverse transfer capacitance		-	90	124	pF
d(on)	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V;	-	13	-	ns
tr	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	120	-	ns
d(off)	turn-off delay time		-	58	-	ns
f	fall time		-	57	-	ns
Source-drai	n diode	· · · · · · · · · · · · · · · · · · ·	1			,
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs;	-	63	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	220	-	nC

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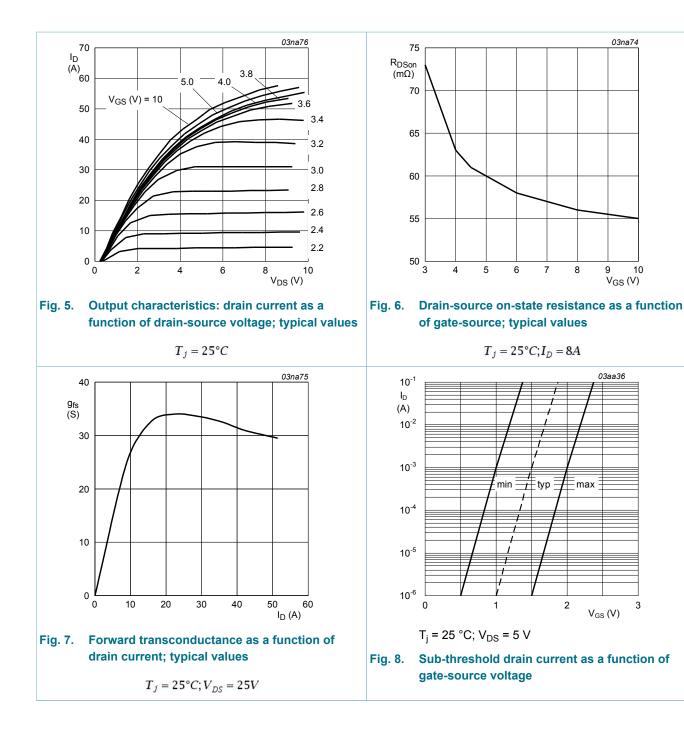
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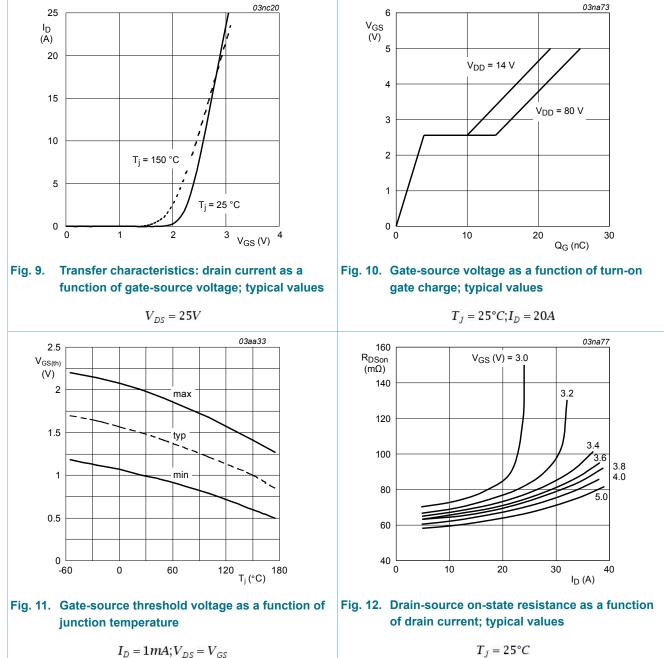
10 $V_{GS}(V)$

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3

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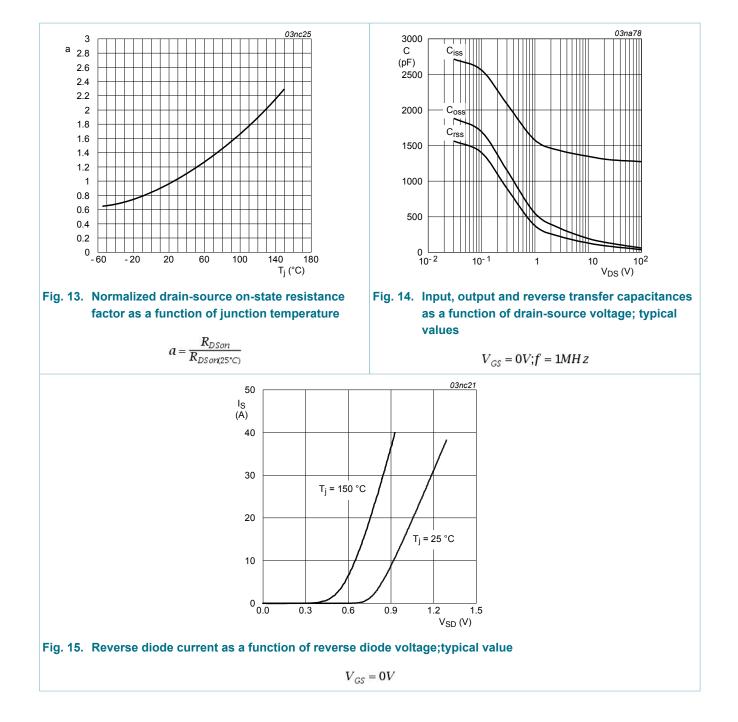


 $I_D = 1 m A; V_{DS} = V_{GS}$



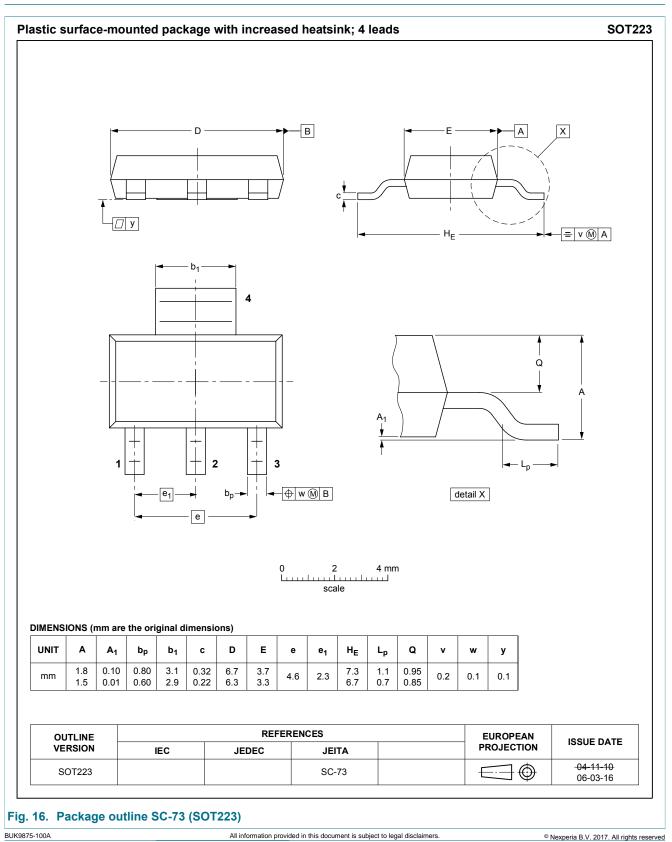
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11. Package outline



Product data sheet

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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